

General Description

The ZM270P03T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

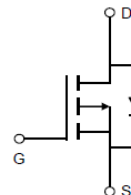
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- Load Switches
- DC/DC
- BLDC Motor driver

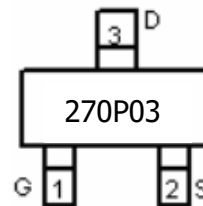
Product Summary



$$V_{DS} = -30V$$

$$R_{DS(ON)} = 27m\Omega$$

$$I_D = -5.1A$$



SOT23-3



Ordering Information:

Marking	270P03
Packing	REEL TAPE
Basic ordering unit (pcs)	3000
Normal Package Material Ordering Code	ZM270P03T-TAP
Halogen Free Ordering Code	ZM270P03T-TAP-HF

Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ TC=25^\circ C$	-5.1	A
	$I_D @ TC=75^\circ C$	-3.9	A
	$I_D @ TC=100^\circ C$	-3.2	A
Pulsed Drain Current ^①	I_{DM}	-12	A
Diode continuous forward current	I_S	-5.1	A
Total Power Dissipation ^②	P_D	1.5	W
Total Power Dissipation	$P_D @ TA=25^\circ C$	0.7	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	30	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	80	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	180	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-30			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-1		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -5A		27	45	mΩ
		V _{GS} = -4.5V, I _D = -2A		39	60	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = -2A		9		S
Source-drain voltage	V _{SD}	I _S = -5A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	850	-	pF
Output capacitance	C _{oss}		-	125	-	
Reverse transfer capacitance	C _{rss}		-	115	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 25V	-	10	-	nC
Gate - Source charge	Q _{gs}	I _D = 8A	-	5	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	6	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

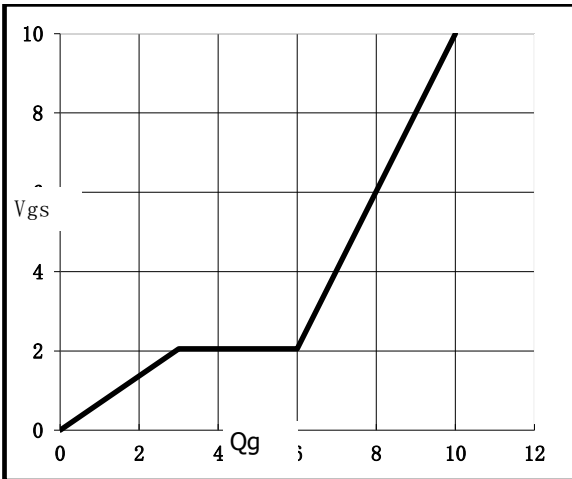


Fig.2 Capacitance Characteristics

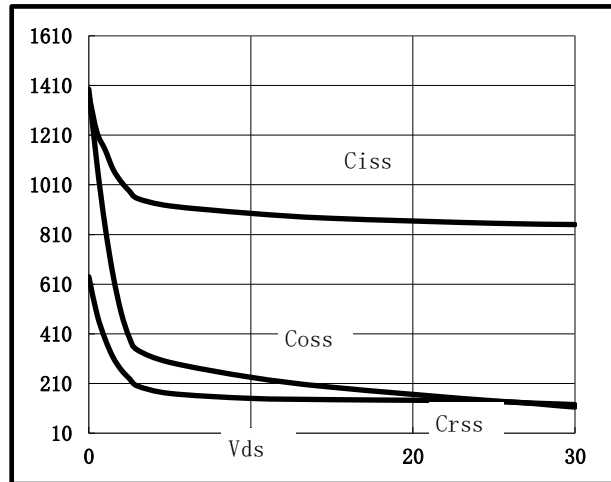


Fig.3 Power Dissipation Derating Curve

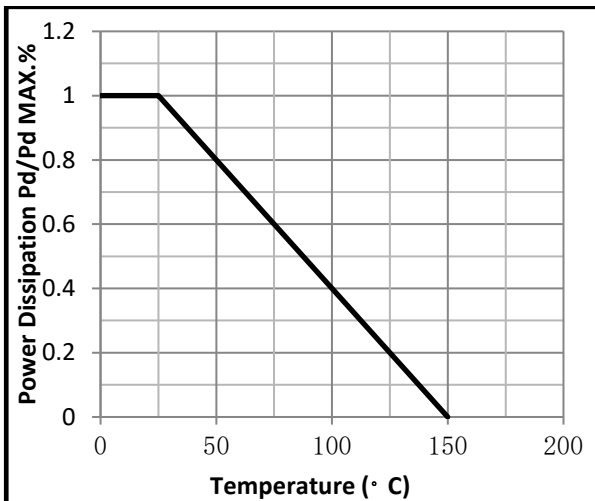


Fig.4 Typical output Characteristics

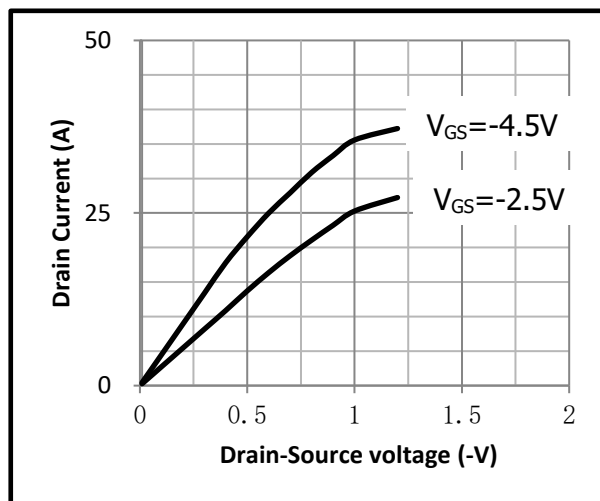


Fig.5 Threshold Voltage V.S Junction Temperature

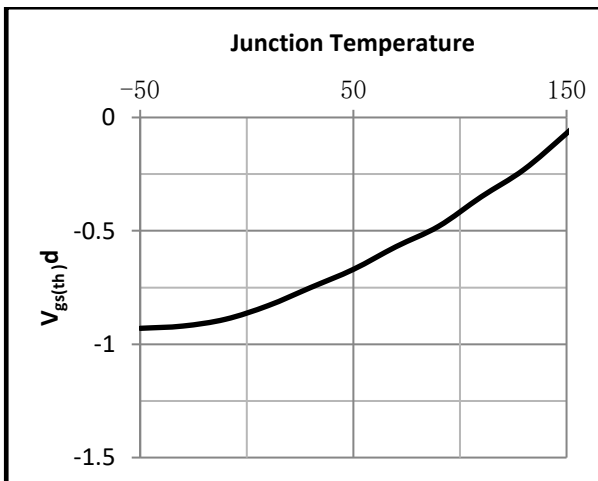


Fig.6 Resistance V.S Drain Current

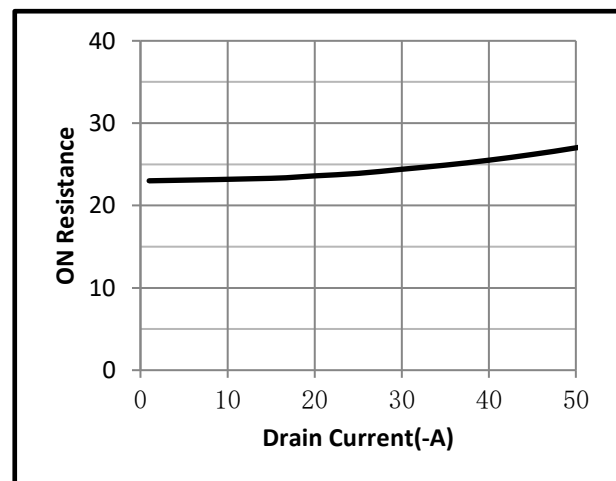


Fig.7 On-Resistance VS Gate Source Voltage

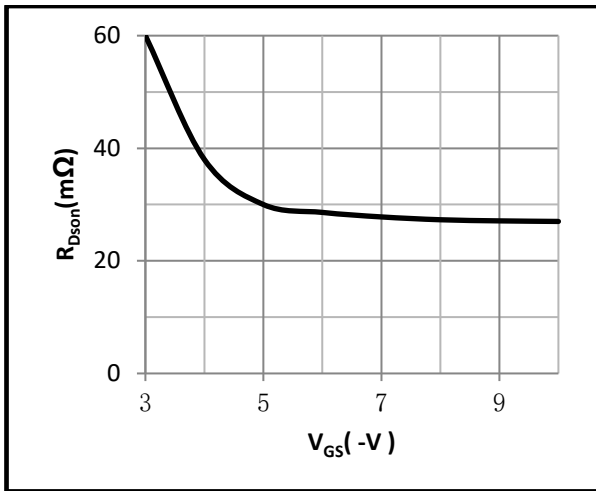


Fig.8 On-Resistance V.S Junction Temperature

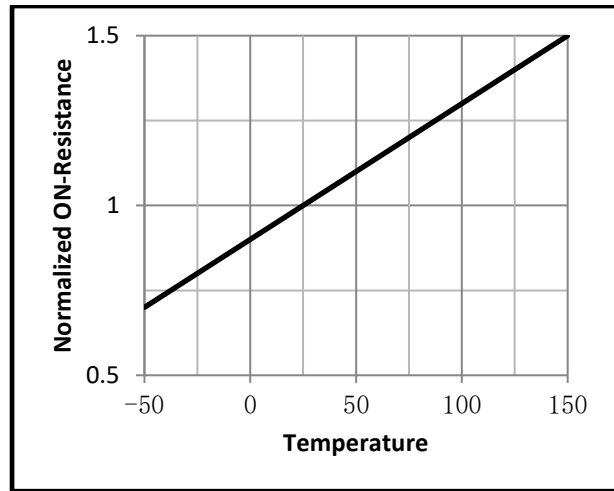


Fig.9 Maximum Forward Biased Safe Operating Area

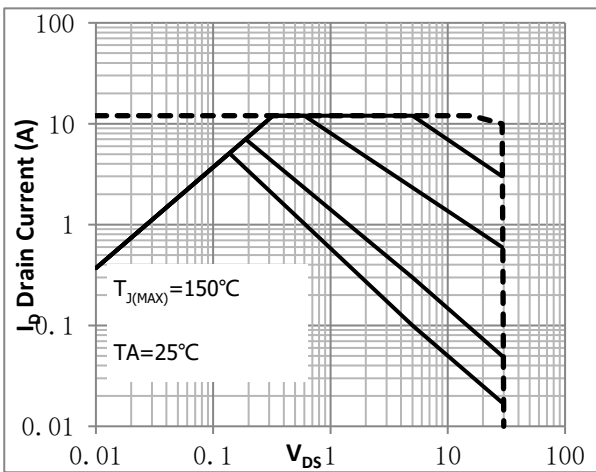


Fig.10 I_D -Junction Temperature

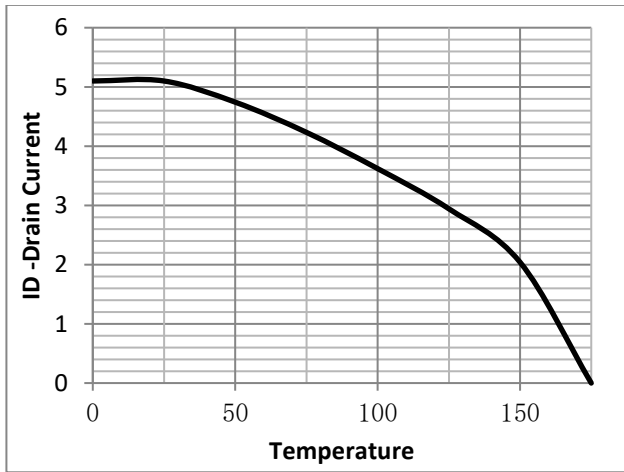


Fig.11 Switching Time Measurement Circuit

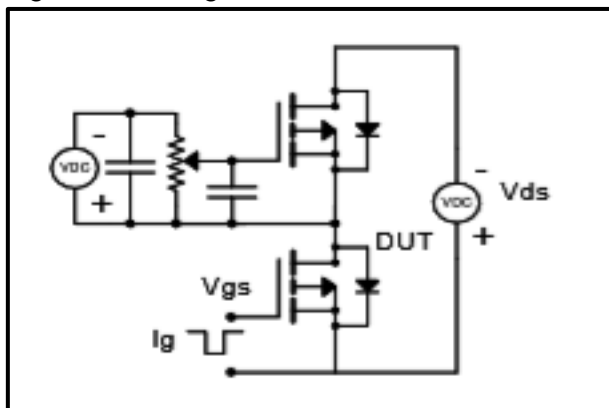


Fig.12 Gate Charge Waveform

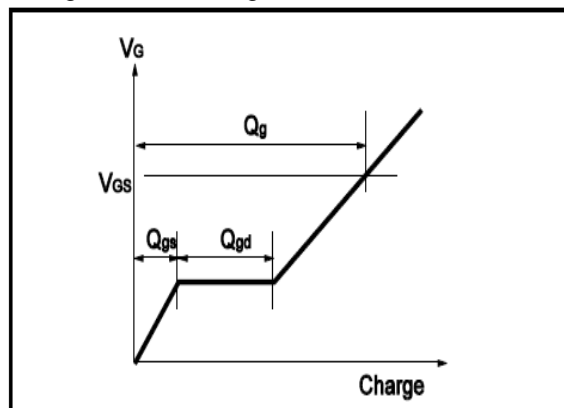


Fig.13 Switching Time Measurement Circuit

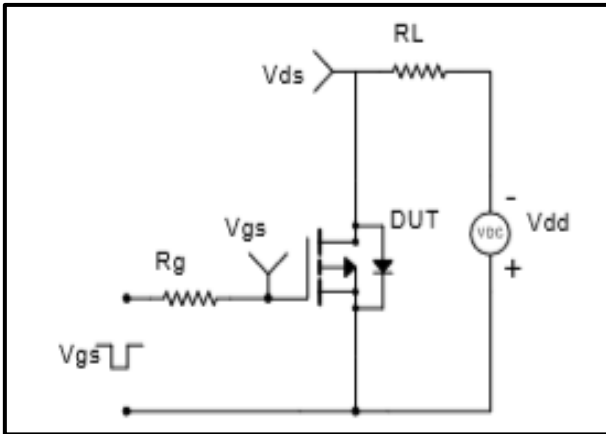


Fig.14 Gate Charge Waveform

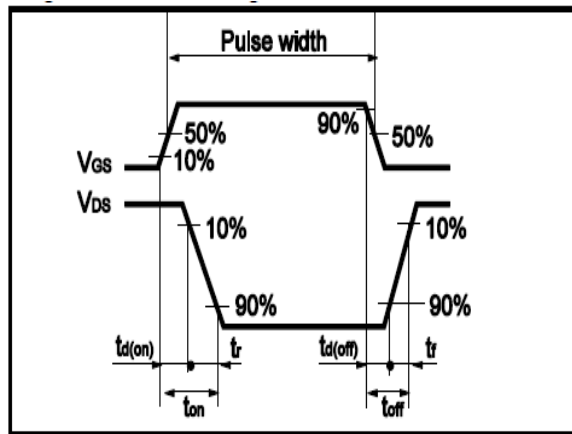


Fig.15 Avalanche Measurement Circuit

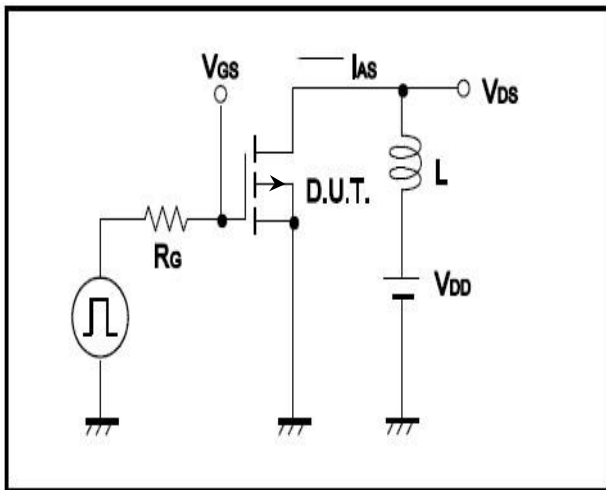
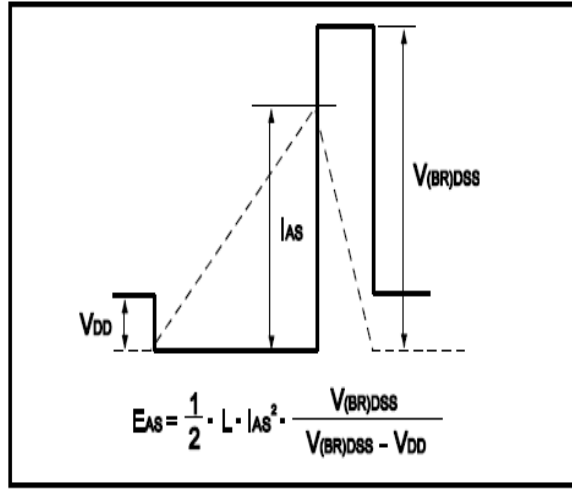
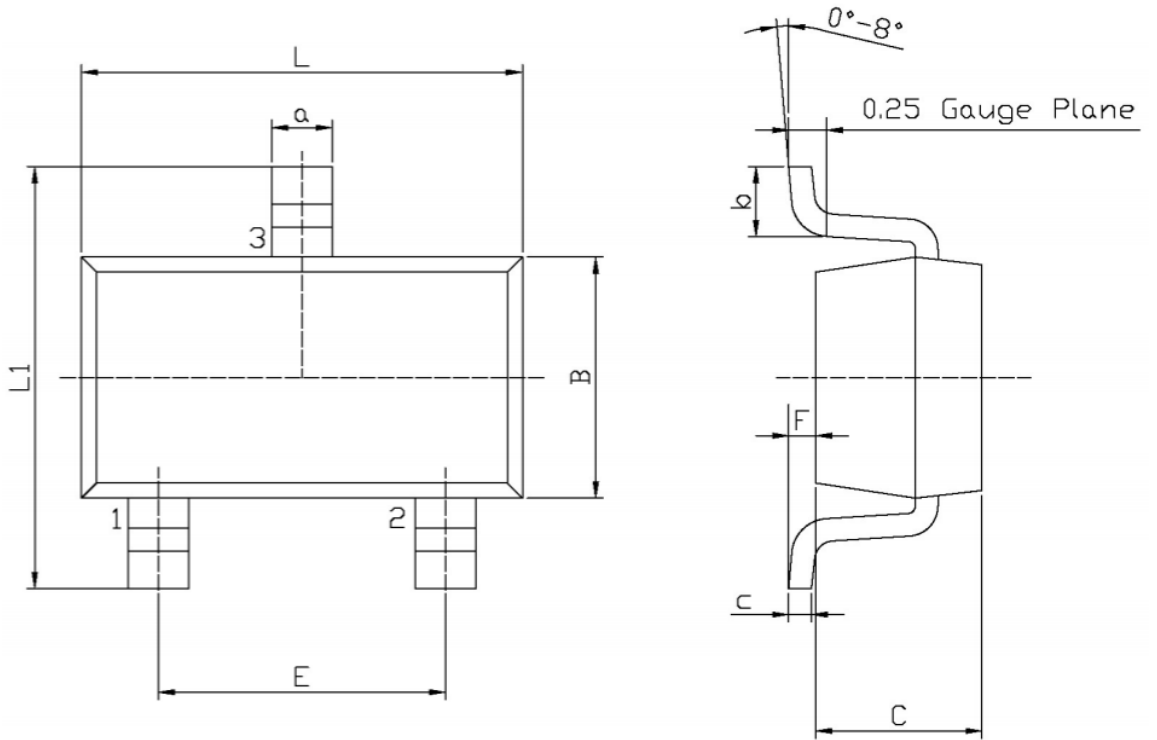


Fig.16vAvalanche Waveform



•Dimensions(SOT23-3)

Unit: mm



Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			

单击下面可查看定价，库存，交付和生命周期等信息

[>>ZMJSEMI\(真茂佳\)](#)